

# NPN SILICON RF POWER TRANSISTOR

45 0

### **DESCRIPTION:**

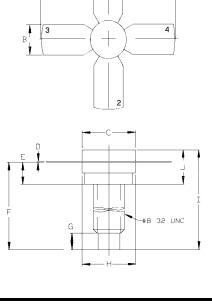
The ASI TPV593 is a Common Emitter Device Designed for Class A High Linearity Television Band IV and V Transmitter Applications.

#### FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- High Gain

#### **MAXIMUM RATINGS**

Ιc	1.2 A
V <sub>CB</sub>	45 V
P <sub>DISS</sub>	17.5 W @ $T_{C} = 25 {}^{O}C$
TJ	-55 <sup>o</sup> C to +200 <sup>o</sup> C
T <sub>STG</sub>	-55 <sup>o</sup> C to +200 <sup>o</sup> C
JC	10 <sup>0</sup> C/W



MINIMUM Inches/mm	MAXIMUM Inches/mm
1.010/25,65	1.055/26,80
.220/5,59	.230/5,84
.270/6.86	285/7,24
.003/0,08	.007/0,18
.117/2,97	.137/3,48
.572	/14,53
.130/	/3.30
.275/6,99	.285/7,24
6402	/16,26
.175/4,45	.21 /75,51
1 = COLLECTOR	
	Inches/mm 1.010/25,65 .220/5,59 .270/6.86 .003/0,08 .117/2,97 .5/2 .130/ .275/6,99 640/ .175/4,45

#### **CHARACTERISTICS** $T_c = 25 °C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV <sub>CEO</sub>	$I_c = 40 \text{ mA}$	26			V
BV <sub>CBO</sub>	$I_c = 10 \text{ mA}$	45			V
BV <sub>EBO</sub>	I <sub>E</sub> = 10 mA	4.0			V
h <sub>FE</sub>	$V_{CE} = 5.0 \text{ V}$ $I_{C} = 250 \text{ mA}$	10			
C <sub>ob</sub>	V <sub>CB</sub> = 28 V f = 1.0 MHz		8.0		pF
P <sub>G</sub>	$\label{eq:sound_carrier} \begin{array}{llllllllllllllllllllllllllllllllllll$	10	12		dB
IMD3	$\label{eq:posterior} \begin{array}{llllllllllllllllllllllllllllllllllll$			-60	dBc

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